

#### Multi-Domain Processors Design Overview

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# **Big picture**



ISCA-2010 Tutorial #2

# **Multi-Domain Processors Design Overview**

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# Why Multi-Domain Processors?



#### **Multi-Domain Processors Design Overview**

- Voltage / frequency scaling basics
- Multi-domain server processors
  - Power gating
  - Core and cache recovery
  - Split vs. connected supplies
  - Globally Asynchronous, Locally Synchronous (GALS)
- Cell phone processors
- Media processors
- Dual voltage supply at the cell level
- Future directions
- Summary

# **Voltage and Frequency Scaling**



#### **Core Power Management States**



# Xeon<sup>®</sup> EX Multi-Core Scaling Trend



### 8-Core Xeon® Processor



#### The largest device count reported for a microprocessor 2.3B transistors

# 8-Core Xeon<sup>®</sup> Processor Clock Domains



#### 8-Core Xeon<sup>®</sup> Processor Voltage Domains



#### Multiple voltage domains minimize power consumption across the core and uncore areas

#### **Core and Cache Recovery Example**



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<sup>[</sup>Rusu, ISSCC 2009] 14

#### **Core Power Gating**

- Resistance target: less than 1% performance loss
- New package-like metal layer on silicon was developed
- M9 has ~10X lower resistance than M8

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#### **Core and Cache Recovery – Infrared Image**



#### All cores and cache slices are enabled



PMU controls processor voltage and frequency based on compute loading and thermal data

Sensors

Core

2

Gate

Power (

Unit

Gate

Power (

Sensors

Core

1

Sensors

Sensors

Core

0

Gate

Power

**Power Gates** 

Gate

Power (

Control

Sensors

Core

3

### 65nm Itanium<sup>®</sup> Processor Domains

	cache r	core	system	Core		1e	
			interface				
Dol	cache	core		core		Voltage (volts)	Frequency (GHz)
			a III a		Core logic	0.9-1.2	Variable
Santa- Lanta- Lanta-	1/2 ap		00		SysInt logic	0.9-1.2	2.4
Latte		Contraction of the second		Antalatatat	IO logic	1.1	2.4
					QR logic	1.1	0.8

### 65nm Itanium<sup>®</sup> Processor Domains



# **Adaptive Voltage and Frequency Control**



### **IBM POWER6 Multi-Rail Design**

 POWER6 infrastructure contains 4 voltage domains

Rail	Purpose	Plot Color
VDD	Logic	All
VCS	Array	Red
VIO	IO, PLL, MC	Blue
VSB	Power-up	Green

- Multi-rail power grid defined based on macro current requirements and iterative IR analysis of each rail.
- Voltage domain of macros and global signals explicitly specified in RTL and validated by checking tools.



# **Split vs. Connected Core Supplies**



### **AMD Barcelona Processor Voltage Domains**

Multiple supplies for power optimization and isolation

- -VDDCORE: 0.8V-1.4V
  - Core and L2: 2.0GHz and up
- -VDDNB: 0.8V-1.4V
  - Northbridge and L3: 75% of core
- -VLDT: 1.2V
  - HyperTransport links
- -VDDIO: 1.8V (VTT:0.9V)
  - DDR I/O
- -VDDA: 2.5V
  - PLLs (10 across the die) + Thermal



# Globally Asynchronous, Locally Synchronous (GALS)



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[P. Teehan, IEEE D&T of C 2007]

25

### Sun/Oracle Niagara2 Clocking



REF	133/167/200 MHz
CMP	1.4 GHz
10	350 MHz
IO2X	700 MHz
FSR.refclk	133/167/200 MHz
FSR.bitclk	1.6/2.0/2.4 GHz
FSR.byteclk	267/333/400 MHz
DR	267/333/400 MHz
PSR.refclk	100/125/250 MHz
PSR.bitclk	1.25 GHz
PSR.byteclk	250 MHz
PCI-Ex	250 MHz
ESR refclk	156 MHz
ESR bitclk	1.56 GHz
ESR byteclk	312.5 MHz
MAC.1	312.5 MHz
MAC.2	156 MHz

# SoC processors must handle multiple clock domains for the various external interfaces

#### **Deterministic Test Mode**



#### Sun/Oracle Rainbow Falls SoC Processor

	MEMO	RY	Mise	<mark>c. IO</mark> =		MEMOR	Y	
	ore Core	Core	Core	Core 4	Core 5	Core 6	Core 7	MEMORY
BC B	L2D 0 CUL21	L2D L20 1 2	D L2D 3 2T1	L2D L 4 L2T	2D L2 5 6 2 1	D L2D 7 2T3		
CLC	U SIU	NCU-	CC 2T5	X L2T	ст.	-2.17		C
	L2D 8	L2D L2I 9 10	D L2D 11	L2D L 12	2D L2 13 1-	D L2D 4 15		RENCY
COHE	ore Core 8 9 COHER	ENCY	Core 11	Core 12	Core 13 COH	Core 14 IEREN	Core 15 CY	COHE

- TSMC 40nm process, 11 ML
- 16 8-threaded SPARC<sup>⊮</sup> cores
- 16KB 8-way Icache
- 64-entry ITLB
- 8KB 4-way Dcache
- 128-entry DTLB
- Enhanced multiply/add FGU and crypto per core
- Unified 6MB 16-bank 24-way L2 cache
- Hierarchical crossbar
- 4 DDR3 channels at 6.4Gbps
- 6 coherency links at 9.6Gbps
- 2x8 PCIe 2.0 at 5GTS
- 2x10G XAUI Ethernet

[Shin, ISSCC 2010]

# Sun/Oracle Rainbow Falls Voltage Domains

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			ET]

Vdd_core (VDDC) 0.8V ~ 1.1V	All Logic	
Vdd_memory 0.9V ~ 1.1V	L2D Memory Cells	
Vdd_analog 1.0V	PLL/SerDes	
VDDT/VDDR 1.5V	I/O	
VNW (VDDC +/- 0.3V)	PMOS Bias	
VNWM	L2D Memory Cells PMOS Bias	
VSB (VSS +/- 0.3V)	NMOS Bias	

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[Shin, ISSCC 2010]

29

### **IBM POWER7<sup>™</sup> Processor**

- 3.0 to 4.14 GHz
- 45nm CMOS SOI
- 567mm<sup>2</sup>
- 1.2B transistors
- Eight processor cores
  - 12 execution units per core
  - 4 Way SMT per core
  - 32 Threads per chip
  - 256KB L2 per core
  - 32MB on chip eDRAM shared L3
  - Dual DDR3 Memory Controllers
    - 100GB/s Memory bandwidth per chip sustained

SMP interface I/O interface SMP interface

30

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#### **P7 Clock Domains**



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[Wendel, ISSCC 2010]

31

#### P7 Voltage Domains (1)

nonnannaine a IGI INT			
	D_EX0 S_EX0 VDD_EX1 VCS_EX1	VDD_EX2 VCS_EX2	_EX3
		VDR_EX2 VDR	EX3
	EX4 VDR_EX5	VDR_EX6 VDR	EX7
	D_EX4 D_EX4 D_EX4 VCS_EX5	VDD_EX6 VCS_EX6 VCS	EX7 EX7
Name: # = 0 to 7	Meaning	Type of Voltage	Min. Max
VDD_EX#	Logic supply for Chiplet #	Adaptive, Dynamic	0.7V 1.3\
VCS_EX#, VDR_EX#	Array supply for chiplet#, DRAM supply for chiplet #	Adaptive, Dynamic	0.8V 1.3V

### P7 Voltage Domains (2)

	VIO S	МТ		
VSB				
VMEM 0	VDD_NEST		VMEM 1	
	VIO SMT			
Name: # = 0 to 7	Meaning	Type of Voltage	Min.	Max.
	Logic supply for pest & pervesive logic	Fixed, Static	1.0V	1.2V
VDD_NEST	Logic supply for nest a pervasive logic			
VDD_NEST VSB	Supply for pervasive	Fixed, Static	1.1V	1.3V
VDD_NEST VSB VMEM 0/1	Supply for pervasive Supply for differential IO	Fixed, Static Fixed, Static	1.1V 0.95V	1.3V 1.15V

### Intel 48-core SoC Processor



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### **Voltage and Frequency Islands**



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# **TI Application Processors**



### Adaptive Voltage Scaling Control Loop



### **Renesas 90nm Cell Phone Processor**



### **Implementation Details**

# of Power domains	20 domains
# of Islands for C4 (Repeaters,CK buffers, BKUP FFs)	19 islands
# of Repeaters in C4 domain	3100 cells
# of Clock buffers in C4 domain	1600 cells
# of Backup FFs in C4 domain	2300 cells
# of μIOs (isolation cell)	20000 cells
Total area of power switch	4.2 mm <sup>2</sup>
Power switch area ratio in the chip	3.4 %
Power-off -> power-on time (one-by-one on)	<100µSec

#### **Renesas 8-Core 90nm Processor**



#### Samsung 3D Graphics Processor

()	Chip Cl	haracteristics
	Technology	0.18um 1-P 6-M CMOS
	Area	Core: 17.2mm <sup>2</sup> Die: 25mm <sup>2</sup>
	Power supply	Core: 1.0V - 1.8V IO: 3.3V
Shader	Frequency	RISC: Max. 200MHz GP: Max. 200MHz RE: Max. 50MHz
	Transistors	1.6M logic, 29KB SRAM
Image: Wertex Cache   Image: Wertex	Processing speed	RISC: 200MIPS VS: 141Mvertices/s RE: 50Mpixels/s
[ RAMP-VI ]	Power consumption	52.4mW @ 60fps 153mW @ full speed

#### Three power domains with independent dynamic voltage-frequency scaling

# **Multiple-Domain Power Management**



### Individually Managed Core Clock Frequency



#### **Power Reduction Benefits**



Much higher benefit achievable with separate voltage domains

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[Yoshida, ISSCC 2007] 45

### **Toshiba's 8-Core Media Processor**



#### **Processor Architecture**





Shutdown MPEs at low work load

### Multi-Domain Processors Design Overview



49

# **Cell-Level Dual-VDD Approach**

- Use reduced voltage VDDL in non-critical paths
- Apply original voltage VDDH to timing critical paths



#### Challenge: minimize number of level converters by clustering

# **Cell-Level Dual-VDD (cont)**



· An intrinsic negative back-biasing of PMOS degrades speed

# **Dual Supply ALU Test Chip Results**



#### **Future Directions for Multi-Core Platforms**



**General Purpose Cores** 

**Special Purpose HW** 

Interconnect fabric

Heterogeneous Multi-Core Platform—SoC

#### **Fine Grain Power Management**



Cores with critical tasks Freq = f, at Vdd TPT = 1, Power = 1

Non-critical cores Freq = f/2, at 0.7xVdd TPT = 0.5, Power = 0.25

Cores shut down TPT = 0, Power = 0

[Adapted from S. Borkar, DAC 2007] 55

#### Summary

- Multiple voltage and clock domains are widely used in modern processor design to manage power and process scaling issues
- Optimize voltage/frequency operating point for each block to minimize power consumption
- The need to shut-off unused logic is driving a finer granularity clock and power gating
- Core and cache recovery enables multiple product options where disabled cores and cache slices are clock and power gated
- Increased use of Globally Asynchronous Locally Synchronous (GALS) clocking for large SoC designs
- Managing all these voltage and frequency domains requires increased software complexity

# Outline



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# The Asynchronous NOC

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